

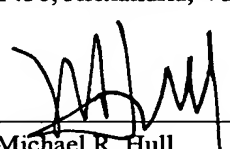


IFW

PATENT
29925/39913

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of: Da-soon Lee
Serial No.: 10/827,456
Filed: April 19, 2004
For: Method for Manufacturing a
Nonvolatile Memory Transistor
Group Art Unit: 2813
Examiner: Jack S.J. Chen

) I hereby certify that this paper and the
) documents referred to as enclosed
) therewith are being deposited with the
) United States Postal Service as first class
) mail, postage prepaid, on **September 30,**
) **2004**, in an envelope addressed to
) Commissioner for Patents, P.O. Box
) 1450, Alexandria, Virginia 22313-1450
)
) 
) Michael R. Hull
) Reg. No. 35,902
) Attorney for Applicants

COMMENT ON STATEMENT OF REASONS FOR ALLOWANCE

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Sir:

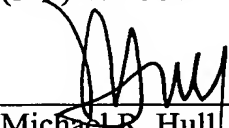
In addition to the reasons for allowance set forth in the allowance papers that were mailed in connection with the present application, it is respectfully submitted that the claims are allowable for the additional reasons that the invention defined by the language of the claims is neither anticipated by, nor would have been obvious when taken as a whole in view of, the art of record.

Respectfully submitted,

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September 30, 2004

By:


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